MOSFETs Silicon P-Channel MOS (U-MOSVI)

# SSM3J356R

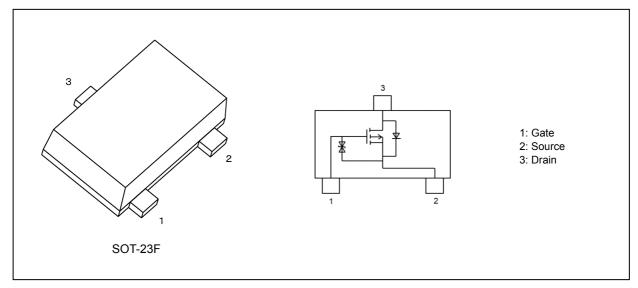
#### 1. Applications

Power Management Switches

#### 2. Features

- (1) AEC-Q101 qualified (Please see the orderable part number list)
- (2) 4 V gate drive voltage.

#### 3. Packaging and Pin Assignment



#### 4. Orderable part number

Orderable part number	AEC-Q101		Note			
SSM3J356R,LF	—		General Use			
SSM3J356R,LXGF	YES	(Note 1)	Unintended Use	(Note 1)		
SSM3J356R,LXHF	YES		Automotive Use			

Note 1: For more information, please contact our sales or use the inquiry form on our website.

#### 5. Absolute Maximum Ratings (Note) (Unless otherwise specified, $T_a = 25$ °C)

	Characteristics			Symbol	Rating	Unit
Drain-source voltage				V <sub>DSS</sub>	-60	V
Gate-source voltage				V <sub>GSS</sub>	-20/+10	
Drain current (DC)			(Note 1)	I <sub>D</sub>	-2	A
Drain current (pulsed)			(Note 1), (Note 2)	I <sub>DP</sub>	-6	
Power dissipation			(Note 3)	PD	1	w
Power dissipation		(t ≤ 10 s)	(Note 3)		2	]
Channel temperature				T <sub>ch</sub>	150	°C
Storage temperature				T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150 °C.
- Note 2: Repetitive rating; pulse width limited by maximum channel temperature.
- Note 3: Device mounted on a 25.4 mm  $\times$  25.4 mm  $\times$  1.6 mm FR4 glass epoxy board (Cu pad: 645 mm<sup>2</sup>)
- Note: This transistor is sensitive to electrostatic discharge and should be handled with care.
- Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.
- Note: The channel-to-ambient thermal resistance, R<sub>th(ch-a)</sub>, and the drain power dissipation, P<sub>D</sub>, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.

### 6. Electrical Characteristics

## 6.1. Static Characteristics (Unless otherwise specified, $T_a = 25$ °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GSS</sub>	V <sub>GS</sub> = -16 V/+10 V, V <sub>DS</sub> = 0 V	_	_	±10	μA
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = -60 V, V <sub>GS</sub> = 0 V		_	-10	μA
Drain-source breakdown voltage		V <sub>(BR)DSS</sub>	I <sub>D</sub> = -1 mA, V <sub>GS</sub> = 0 V	-60	_	_	V
Drain-source breakdown voltage	(Note 1)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = -1 mA, V <sub>GS</sub> = 10 V	-50	_	_	
Gate threshold voltage		V <sub>th</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1 mA	-0.8	_	-2.0	V
Drain-source on-resistance	(Note 2)	R <sub>DS(ON)</sub>	$I_D$ = -1.0 A, $V_{GS}$ = -4.0 V	_	280	400	mΩ
			I <sub>D</sub> = -1.0 A, V <sub>GS</sub> = -4.5 V	_	270	360	
			I <sub>D</sub> = -1.0 A, V <sub>GS</sub> = -10 V		240	300	]
Forward transfer admittance	(Note 2)	Y <sub>fs</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1 A	_	4.7	—	S

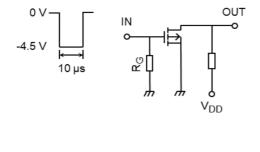
Note 1: If a reverse bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drainsource breakdown voltage is lowered in this mode.

Note 2: Pulse measurement.

## 6.2. Dynamic Characteristics (Unless otherwise specified, $T_a = 25$ °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V,	_	330	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	_	25	_	
Output capacitance	C <sub>oss</sub>		_	40	_	
Switching time (turn-on time)	t <sub>on</sub>	V <sub>DD</sub> = -30 V, I <sub>D</sub> = -1.0 A V <sub>GS</sub> = 0 to -4.5 V, R <sub>G</sub> = 10 Ω		29	_	ns
Switching time (turn-off time)	t <sub>off</sub>	$\begin{array}{l} Duty \leq 1 \%,  V_{IN} \!\!: t_r,  t_f < 5  ns, \\ Common  source,  See  Chapter  6.3. \end{array}$	_	48	—	

### 6.3. Switching Time Test Circuit



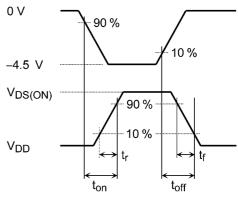


Fig. 6.3.1 Switching Time Test Circuit

Fig. 6.3.2 Input Waveform/Output Waveform

### 6.4. Gate Charge Characteristics (Unless otherwise specified, $T_a = 25$ °C)

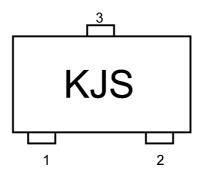
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)		$V_{DD}$ = -48 V, $V_{GS}$ = -10 V,	_	8.3	—	nC
Gate-source charge 1	Q <sub>gs1</sub>	I <sub>D</sub> = -2.0 A	_	0.8	_	
Gate-drain charge	Q <sub>gd</sub>		_	1.7	_	

### 6.5. Source-Drain Characteristics (Unless otherwise specified, $T_a = 25$ °C)

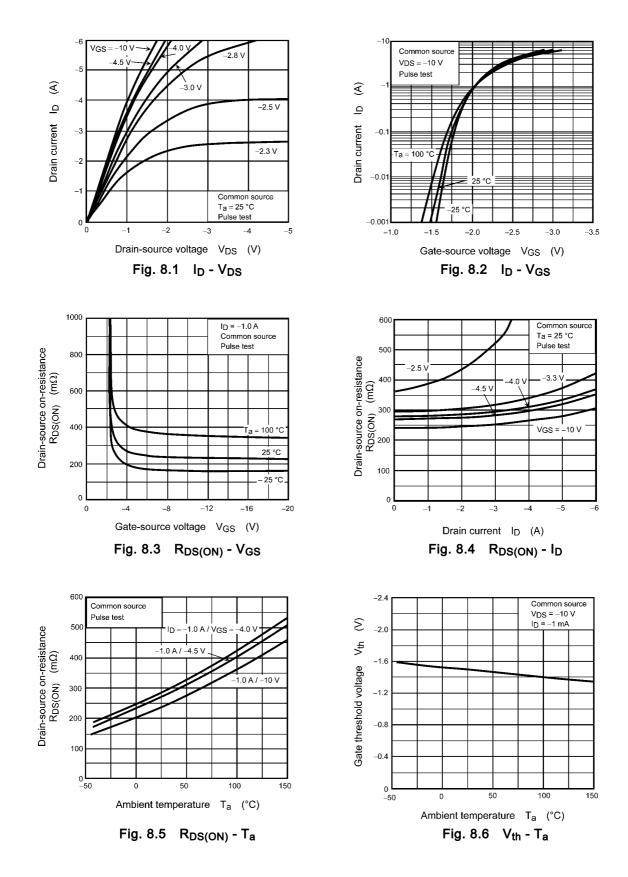
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage (	Note 1)	$V_{\text{DSF}}$	$I_D$ = 2.0 A, $V_{GS}$ = 0 V		0.9	1.2	V

Note 1: Pulse measurement.

#### 7. Marking



8. Characteristics Curves (Note)





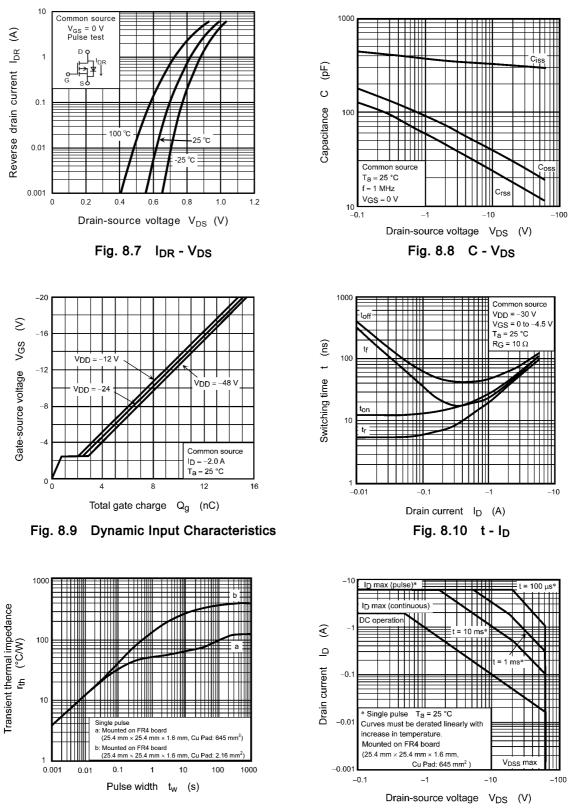
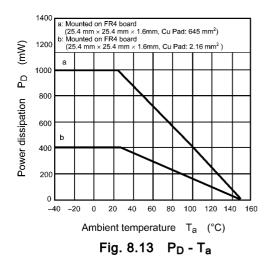


Fig. 8.12 Safe Operating Area

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Fig. 8.11 r<sub>th</sub> - t<sub>w</sub>





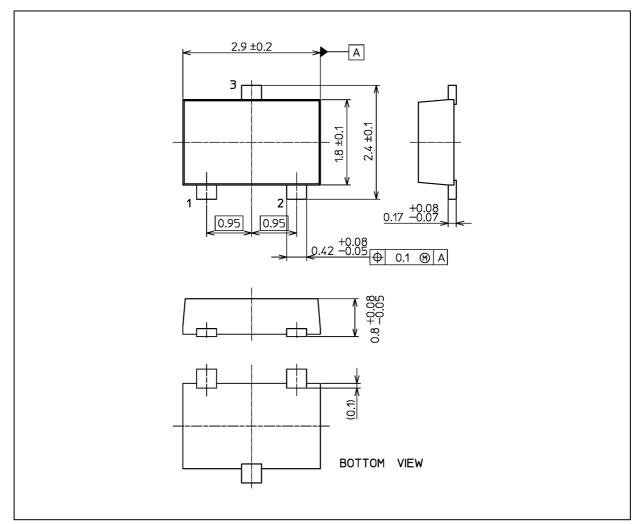
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## SSM3J356R

#### Package Dimensions

Unit: mm



Weight: 0.011 g (typ.)

	Package Name(s)
TOSHIBA: 2-3Z1S	
Nickname: SOT-23F	

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